

December 2013

FQP6N40C

N-Channel QFET® MOSFET

400 V, 6.0 A, 1.0 Ω

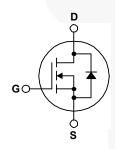
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 6.0 A, 400 V, $R_{DS(on)} = 1.0 \Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_{D} = 3 \text{ A}$
- Low Gate Charge (Typ. 16 nC)
- · Low Crss (Typ. 15 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP6N40C	Unit	
V _{DSS}	Drain-Source Voltage		400	V	
I _D	Drain Current - Continuous (T _C = 25°C)		6	А	
	- Continuous (T _C = 100°C)		3.6	Α	
I _{DM}	Drain Current - Pulsed (Note 1)	24	Α	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	270	mJ	
I _{AR}	Avalanche Current (Note 1)	6	А	
E _{AR}	Repetitive Avalanche Energy (Note 1)	7.3	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note		4.5	V/ns	
P_D	Power Dissipation (T _C = 25°C)		73	W	
	- Derate above 25°C		0.58	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.		300	°C	

Thermal Characteristics

Symbol	Parameter	FQP6N40C	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.71	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP6N40C	FQP6N40C	TO-220	Tube	N/A	N/A	50 units

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	400			V
ΔBV_{DSS}	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.54		V/°C
I _{DSS}	Zone Oode Welfere Breis Oomen	V _{DS} = 400 V, V _{GS} = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 320 V, T _C = 125°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse V _{GS} = -30 V, V _{DS} = 0 V				-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 3A		0.83	1	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 3 \text{A}$		4.7		S
Dvnam	ic Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		480	625	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		80	105	pF
C _{rss}	Reverse Transfer Capacitance			15	20	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V 000 V I 00		13	35	ns
t _r	Turn-On Rise Time	$V_{DD} = 200 \text{ V}, I_D = 6A,$		65	140	ns
t _{d(off)}	Turn-Off Delay Time	$R_G = 25 \Omega$		21	55	ns
t _f	Turn-Off Fall Time	(Note 4)		38	85	ns
Qg	Total Gate Charge	$V_{DS} = 320 \text{ V}, I_{D} = 6A,$		16	20	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 328 \text{ V}, I_D = 374,$		2.3		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	/	8.2		nC
Drain S	Source Diede Characteristics of	nd Maximum Batings				
l _S	Source Diode Characteristics and Maximum Continuous Drain-Source Dic				6	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F				24	A
V _{SD}	Drain-Source Diode Forward Voltage				1.4	V
	= Ood. oo = .odo i oi ii ala voitago	00 - , 0			7	•
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{S} = 6 \text{ A},$		230		ns

Notes:
1. Repetitive rating : pulse-width limited by maximum junction temperature.
2. L = 13.7 mH, I_{AS} = 6 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C .
3. $I_{SD} \le 6$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.
4. Essentially independent of operating temperature.

Typical Characteristics

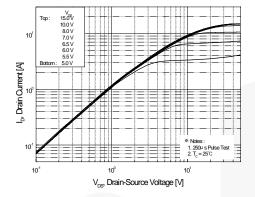


Figure 1. On-Region Characteristics

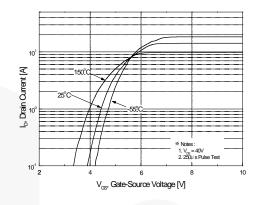


Figure 2. Transfer Characteristics

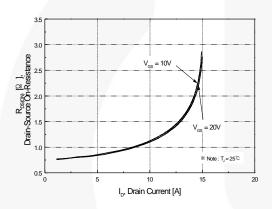


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

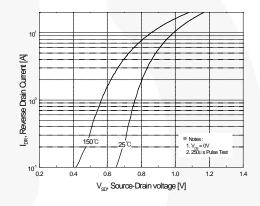


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

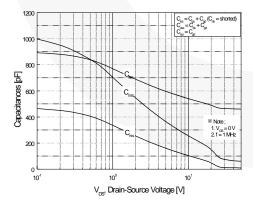


Figure 5. Capacitance Characteristics

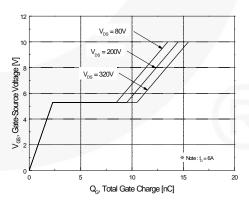
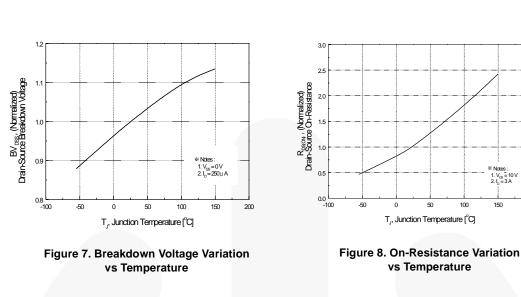
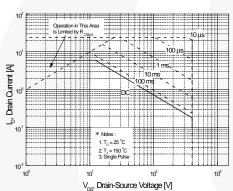


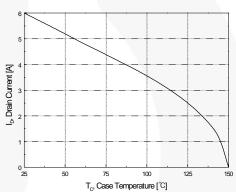
Figure 6. Gate Charge Characteristics





Typical Characteristics (Continued)

Figure 9. Maximum Safe Operating Area



150

Figure 10. Maximum Drain Current vs Case Temperature

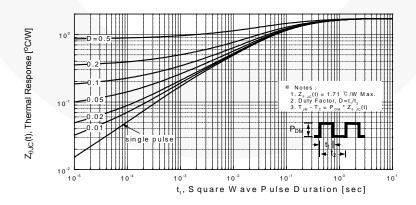


Figure 11. Transient Thermal Response Curve

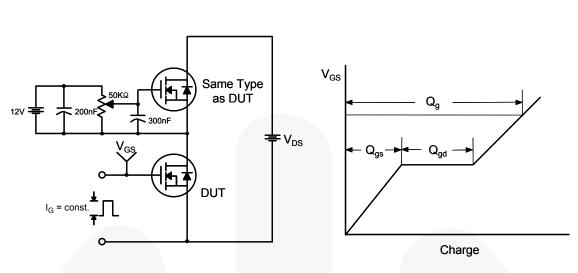


Figure 12. Gate Charge Test Circuit & Waveform

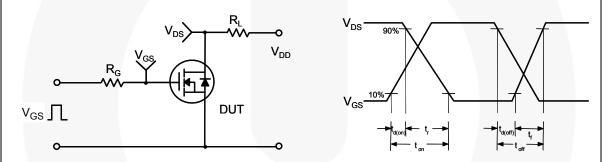


Figure 13. Resistive Switching Test Circuit & Waveforms

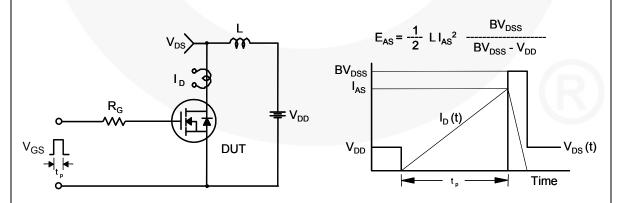
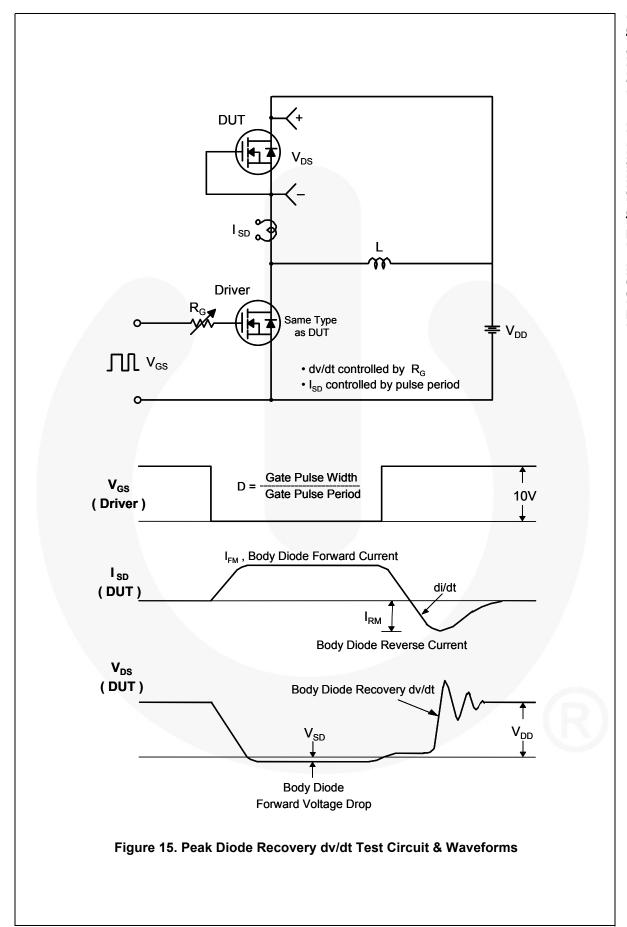


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

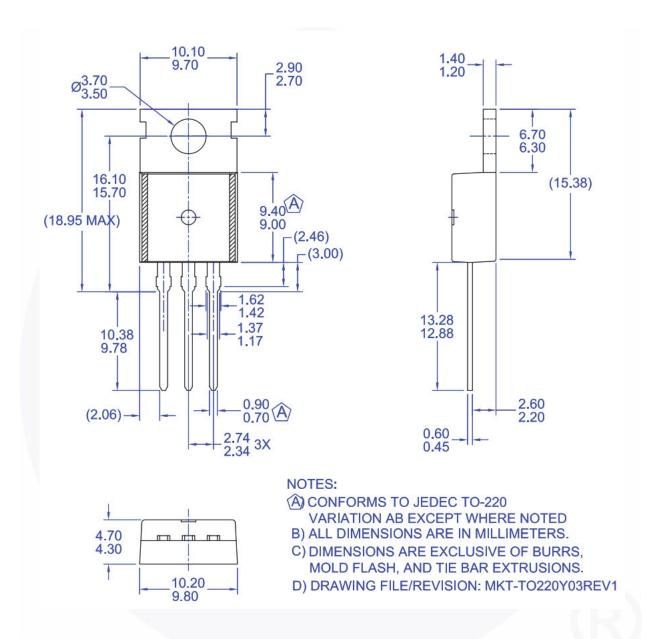


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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